

Silicon NPN Power Transistors

2SC1295

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

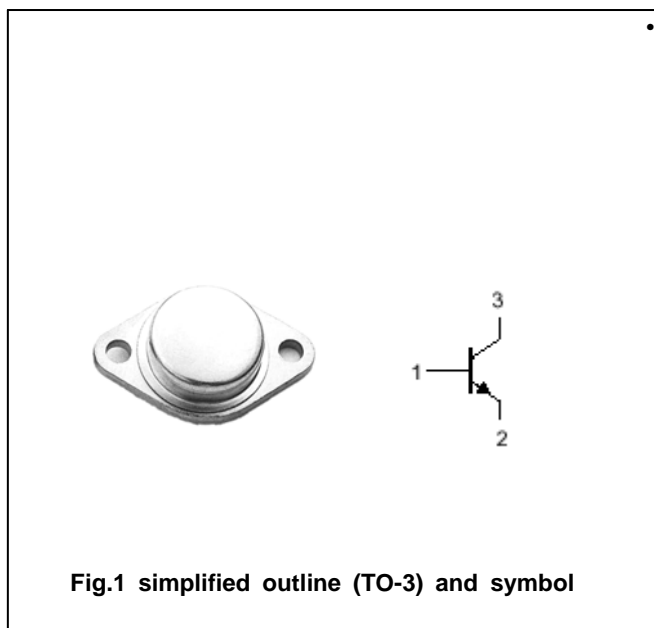


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	350	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	350			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2 A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2 A; I _B =1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1.5A ; V _{CE} =5V	3		13	

PACKAGE OUTLINE

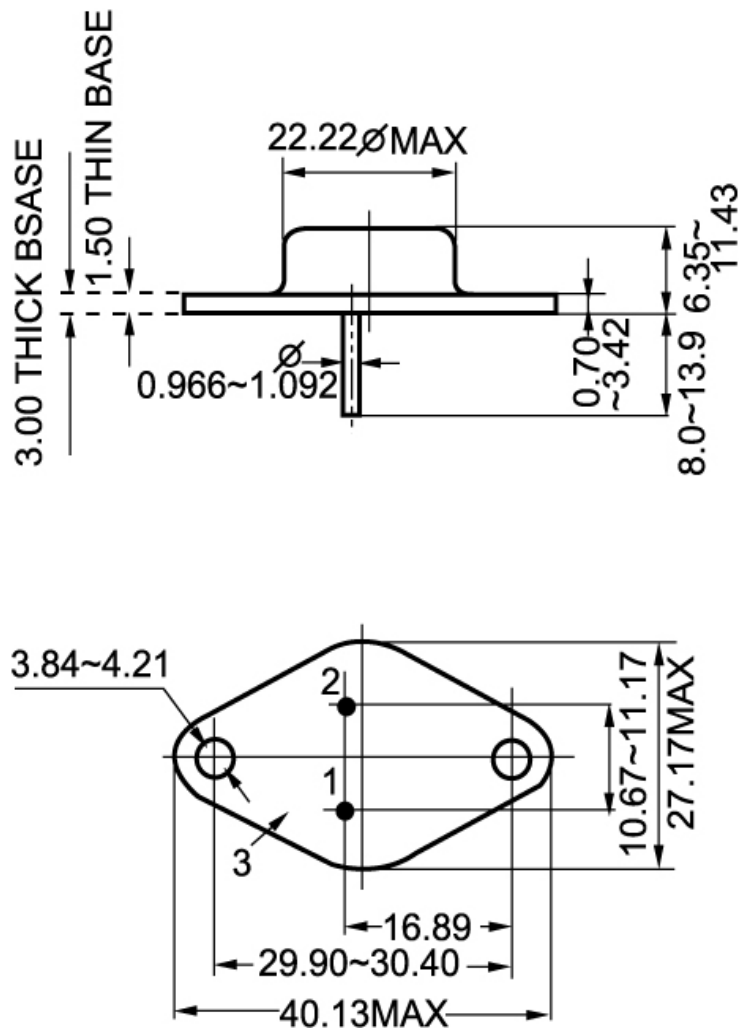


Fig.2 Outline dimensions